

S/N: 10/556,063

3/9/2007

Docket No.: SUG-187-PCT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Serial No.: 10/556,063

Confirmation No.: 4291

Applicant: Masatoshi TAKAHASHI, et al.

Art Unit: TO BE ASSIGNED

Filed: November 8, 2005

Examiner: TO BE ASSIGNED

Docket No: SUG-187-PCT

Customer No: 28892

For: Solar Cell and Method of Fabricating the Same

INFORMATION DISCLOSURE STATEMENT
PURSUANT TO 37 C.F.R. §§ 1.56, 1.97, and 1.98

US Patent & Trademark Office
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Randolph Building
401 Dulany Street
Alexandria, VA 22314

Sir:

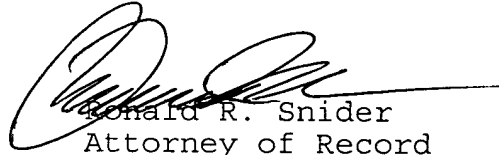
In compliance with the dictates of 37 C.F.R. §§ 1.56, 1.97, and 1.98, Applicant hereby submits an Information Disclosure Statement.

Applicant hereby reports the issuance of an International Search Report in the Japanese application and a Supplementary European Search Report. A copy of these Search Reports and references cited therein as well as other relevant documents, together with PTO Form 1449 listing each of the references is attached hereto. In accordance with MPEP § 609 III A(2), copies of US patent documents are not attached for applications filed after June 30, 2003 (MPEP Rev. 2, May 2004, page 600-128).

INFORMATION DISCLOSURE STATEMENT TRANSMITTAL - PAGE 2

It is respectfully requested that the Examiner consider each of these references and indicate such consideration by enclosing an appropriately initialled copy of the enclosed form PTO-1449 with the next communication from the Patent Office.

Respectfully submitted,


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Date: March 9, 2007

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INFORMATION DISCLOSURE STATEMENT - PTO FORM 1449

U.S. PATENT DOCUMENTS			
Examiner Initials*	U.S. Patent Document Number	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
	2002/0086557	Matsumura et al.	July 4, 2002
	6,349,669 (JP 10-83988)	Matsumura et al.	Feb. 26, 2002
	6,291,366	Sano et al.	Sept. 18, 2001
	6,225,241 (JP 10-209151)	Miyoshi	May 1, 2001
	6,069,094	Matsumura et al.	May 30, 2000

INFORMATION DISCLOSURE STATEMENT - PTO FORM 1449 - PAGE 2 OF 3

FOREIGN PATENT DOCUMENTS				
Examiner Initials*	Foreign Patent Document Number	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T**
	JP 2002-75877 (w/ Eng. Abstract)	Manabu et al.	March 15, 2002	
	JP 2000-216163 (w/ Eng. Abstract)	Fujitsu Ltd.	August 4, 2000	
	JP 10-209151 (US 6,225,241)	NEC Corp.	August 7, 1998	
	JP 10-83988 (US 6,349,669)	Hideki Matsumura	March 31, 1998	
	JP 9-205209 (w/ Eng. Abstract)	Yoda Masato	August 5, 1997	
	JP 9-97916 (w/ Eng. Abstract)	Sharp Corp.	April 8, 1997	
	JP 8-250438 (w/ Eng. Abstract)	Hideki et al.	Sept. 27, 1996	
	JP 8-55858 (US 6,291,366)		Feb. 27, 1996	
	JP 6-291114 (w/ Eng. Abstract)	Fuse Akihiro	Oct. 18, 1994	
	EP 325606	Mobil Solar Energy Corp.	Sept. 7, 1994	
	JP 2-500397 (WO 89/00341)	Mobil Solar Energy Corp.	Feb. 8, 1990	
	WO 89/00341 (JP 2-500397)	Chaudhuri et al.	January 12, 1989	

INFORMATION DISCLOSURE STATEMENT - PRO FORM 1449 - PAGE 3 OF 3

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS		
Examiners Initials *	Include Author (CAPITAL LETTERS), title of article, book, magazine, etc. date, page(s), volume-issue number(s), publisher, city and/or country where published	T**
	HOLT, J.K. et al., "Hot-Wire Chemical Vapor Deposition of High Hydrogen Content Silicon Nitride for Solar Cell Passivation and Anti-Reflection Coating Applications", <u>Elsevier Science B.V.</u> , April 2003, pp. 37-40, Vol. 430, No. 1-2.	
	MOSCHNER, JENS D. et al., "Thermo-Catalytic Deposition of Silicon Nitride - A New Method for Excellent Silicon Surface Passivation," 29th IEEE Photovoltaic Specialists Conference, New Orleans, May 20-24, 2002, pp.174-177.	
	MATSUMURA, H. et al., "CAT-CVD Process and Its Application to Preparation of Si-Based Thinfilms", Materials Research Society Symposium Proceedings, San Francisco, April 5-9, 1999, pp. 67-78, Vol., 557.	
	KUDO, A. et al., "Study on Improvement on Uniformity of Cat-CVD SiNx Thin Films", <u>Technical Report of IEICE</u> , April 1999, pp. 59-66, ED99-10.	
	OKADA, SHINYA et al., "Improved Properties of Silicon Nitride Films Prepared by the Catalytic Chemical Vapor Deposition Method," <u>Japan Journal Applied Physics</u> , Nov. 1997, pp. 7035-7040, Vol. 36, No. 11.	

Examiner Signature		Date Considered	
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***Examiner:** Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

****Applicant** is to place a check mark here if English language translation is attached